Ordering number : ENN7036

P-Channel Silicon MOSFET

EC4303C

Small Signal Switch, Interface Applications

Features

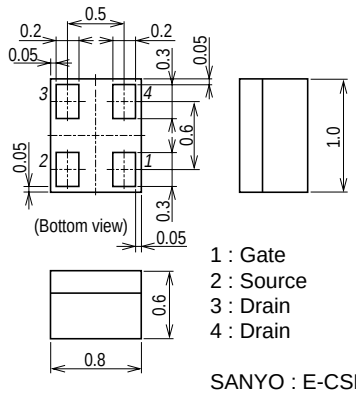
- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Package Dimensions

unit : mm

2197

[EC4303C]



1 : Gate
2 : Source
3 : Drain
4 : Drain

SANYO : E-CSP1008-4

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−50	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		−0.07	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−0.28	A
Allowable Power Dissipation	P_D		0.15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0	−50			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−50V, V_{GS}=0			−10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=−10V, I_D=−100μA	−1		−2.5	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=−10V, I_D=−40mA	50	70		mS
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=−40mA, V_{GS}=−10V		17	22	Ω
	$R_{DS}(on)2$	I_D=−20mA, V_{GS}=−4V		23	32	Ω

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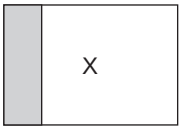
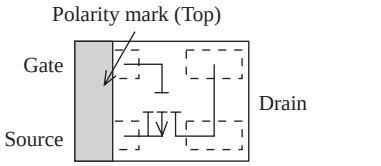
Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		6.2		pF
Output Capacitance	Coss	V_{DS}=–10V, f=1MHz		4.0		pF
Reverse Transfer Capacitance	Crss	V_{DS}=–10V, f=1MHz		1.3		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		13		ns
Rise Time	t_{r}	See specified Test Circuit.		10		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit.		100		ns
Fall Time	t_{f}	See specified Test Circuit.		150		ns
Total Gate Charge	Qg	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–70mA		1.32		nC
Gate-to-Source Charge	Qgs	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–70mA		0.17		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=–10V, V_{GS}=–10V, I_{D}=–70mA		0.34		nC
Diode Forward Voltage	V_{SD}	I_{S}=–70mA, V_{GS}=0		–0.85	–1.2	V

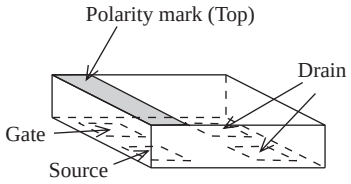
Type No. Indication(Top view)



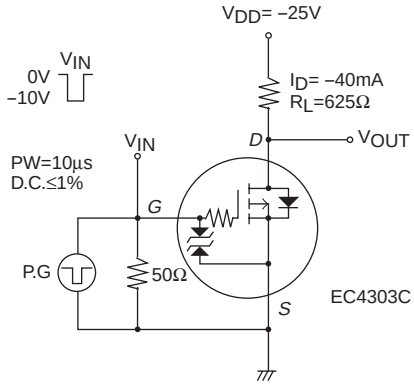
Electrical Connection(Top view)

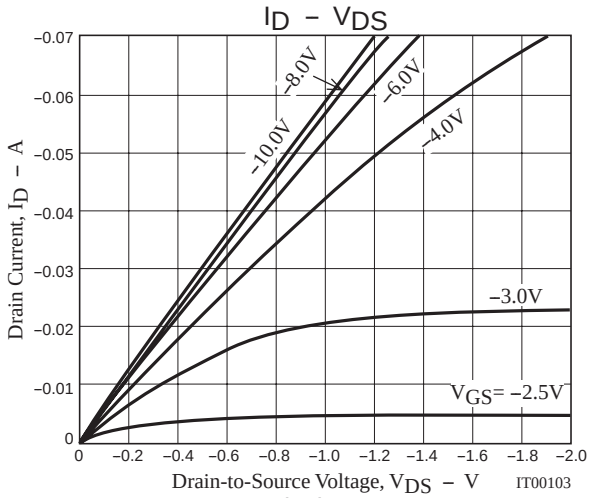


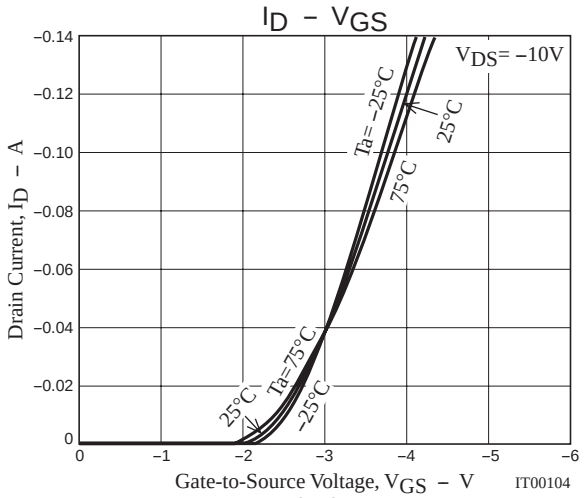
*Electrodes : on the bottom

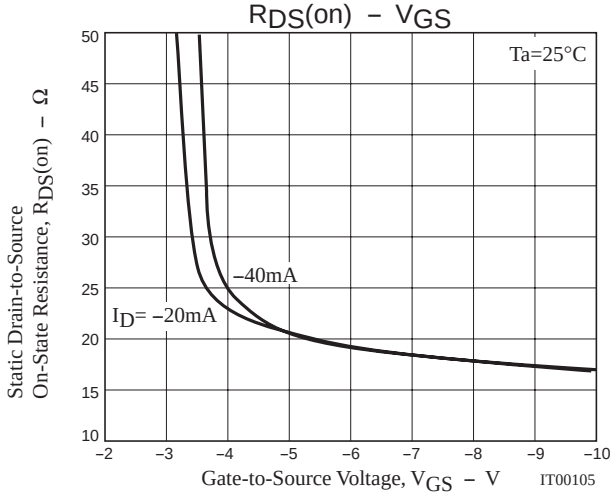


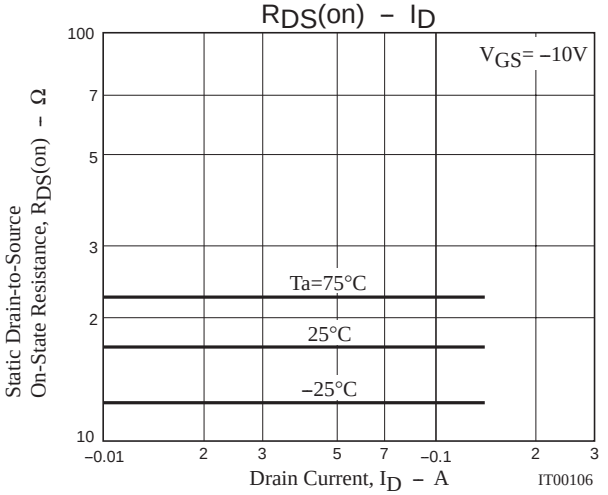
Switching Time Test Circuit

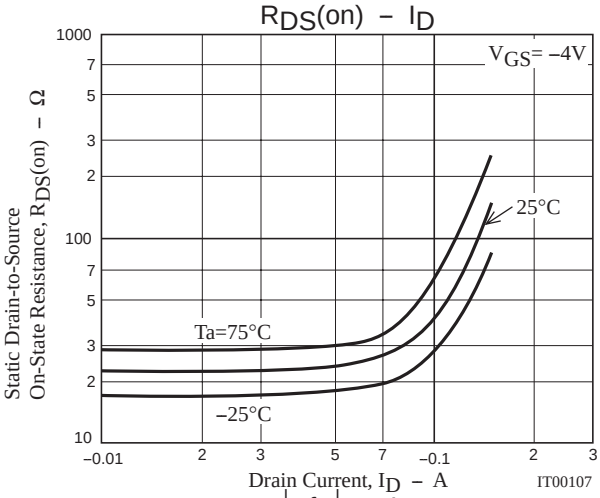


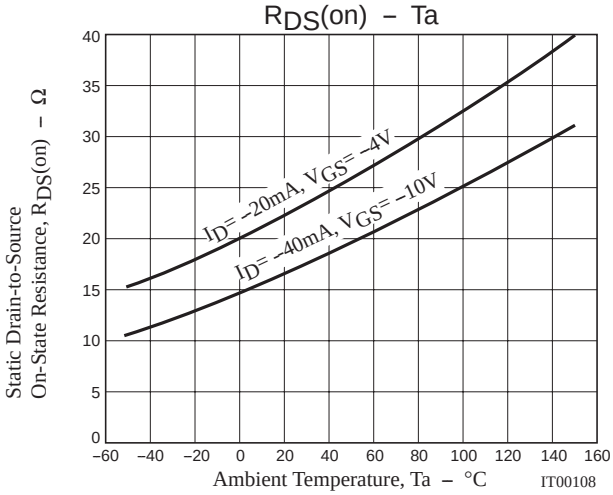


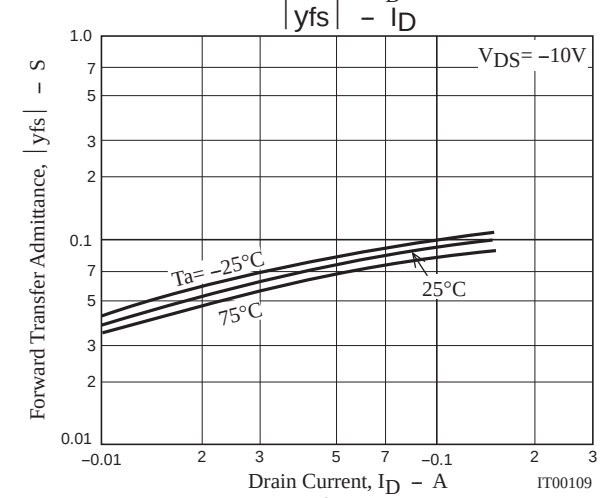


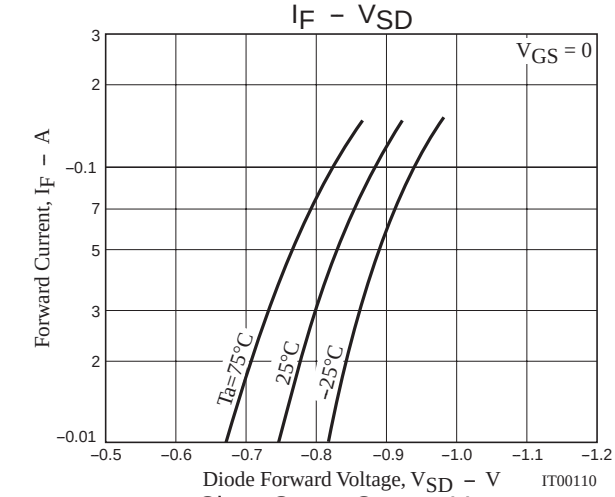


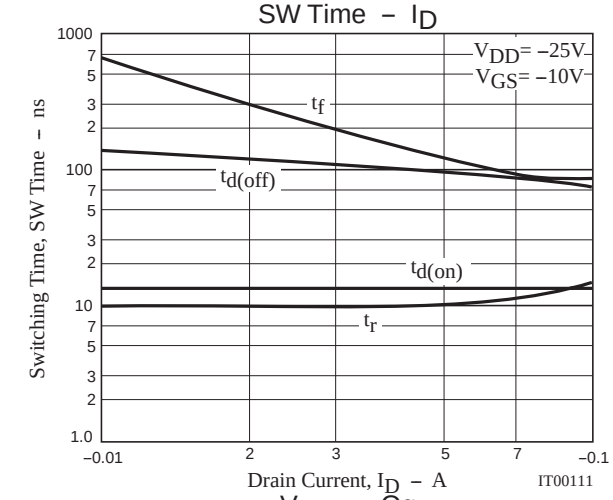


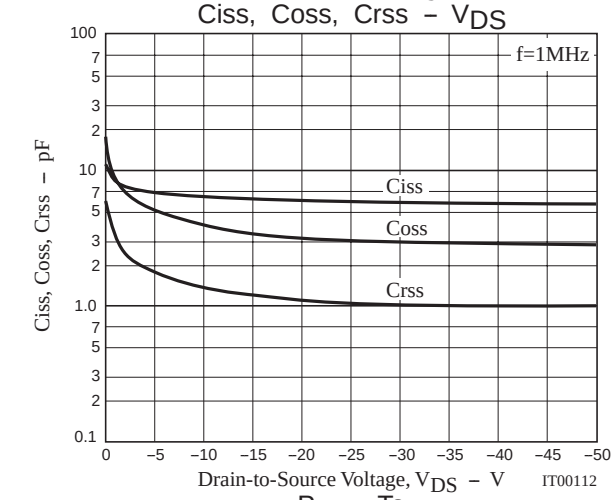

RDS(on) – ID
VGS= –4V
25°C
Ta=75°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00107

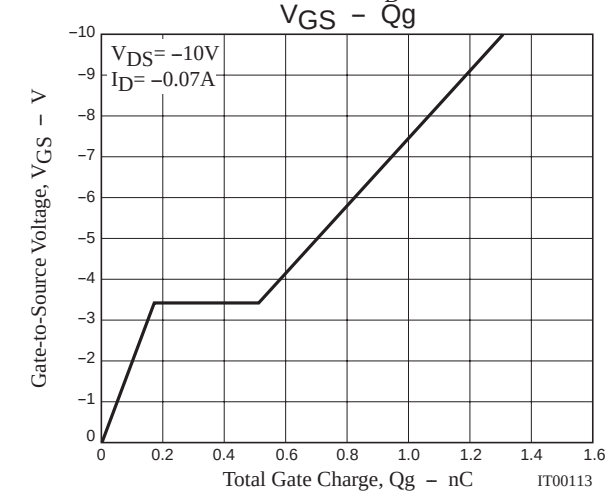

RDS(on) – Ta
ID= –20mA, VGS= –4V
ID= –40mA, VGS= –10V
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Ambient Temperature, Ta – °C
IT00108

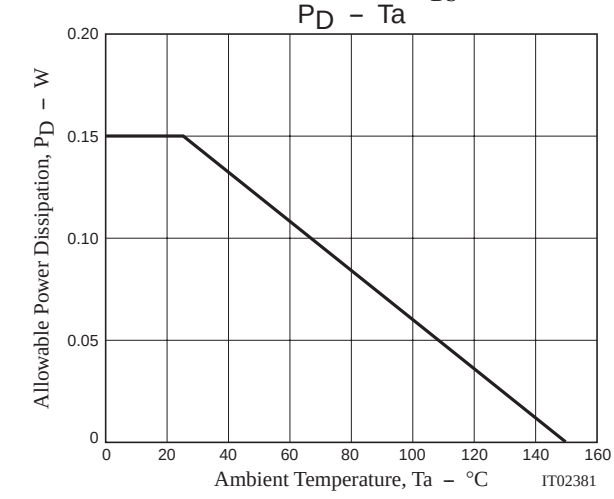

|yfs| – ID
VDS= –10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT00109


IF – VSD
VGS = 0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT00110


SW Time – ID
VDD= –25V
VGS= –10V
tf
td(off)
td(on)
tr
Switching Time, SW Time – ns
Drain Current, ID – A
IT00111


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT00112


VGS – Qg
VDS= –10V
ID= –0.07A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT00113


PD – Ta
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT02381

Note on usage : Since the EC4303C is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.